A new approach to crystal silicon thin films on glass

Goal: c-Si on glass

- Material quality of crystal silicon
- Economics of thin films

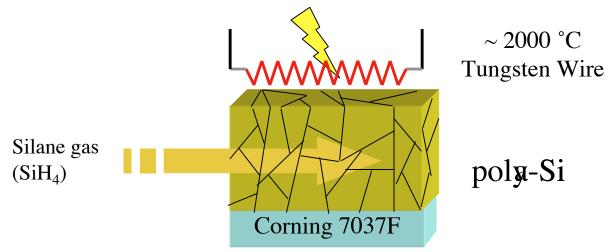
Chaz Teplin, Howard Branz,
David Ginley, Eugene Iwaniczko,
Kim Jones, Mowafak Al-Jassim,
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Another approach to thin film silicon

Goal: Silicon on glass

- Quality of crystal silicon
- Economics of thin films

It's "easy" to make bad thin film c-Si



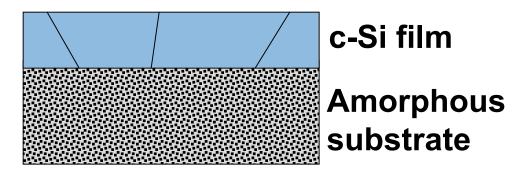
Substrate Temp. 275-425 °C

Results in Poor Material

- Small grains
- Random grain orientation (polycrystalline)

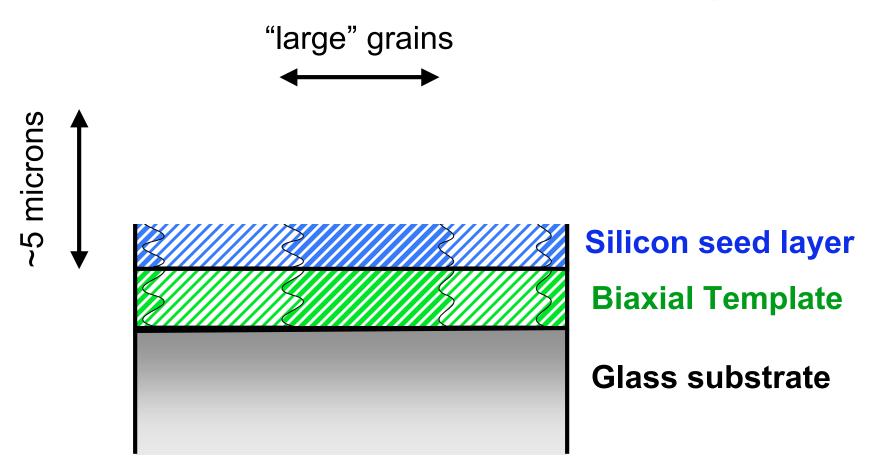
Desired c-Si film properties

- Large grains
- Uniformly oriented grains (biaxial texture)
 - Passivated grain boundaries



The crucial challenge: Substrate/c-Si interface

Proposed route to c-Si on glass

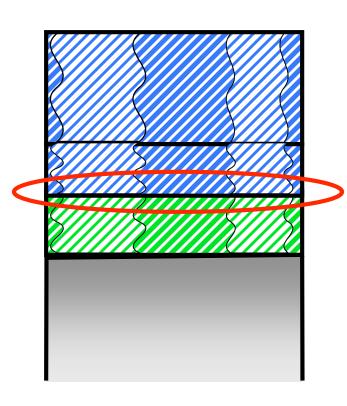


The template/c-Si interface

Goal

Attain a silicon seed layer with biaxial texturing

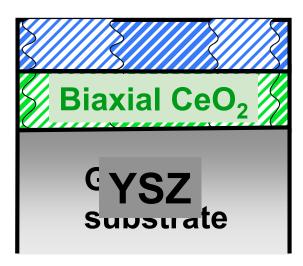
Potential template materials CeO₂, NiSi, CoSi, ZrO₂, TiN



First template: CeO₂

- Lattice matched to silicon
- Safe, abundant, stable material
- Has been grown with biaxial texture on glass
- Not conductive
 - Eliminates some device structures

c-Si seed

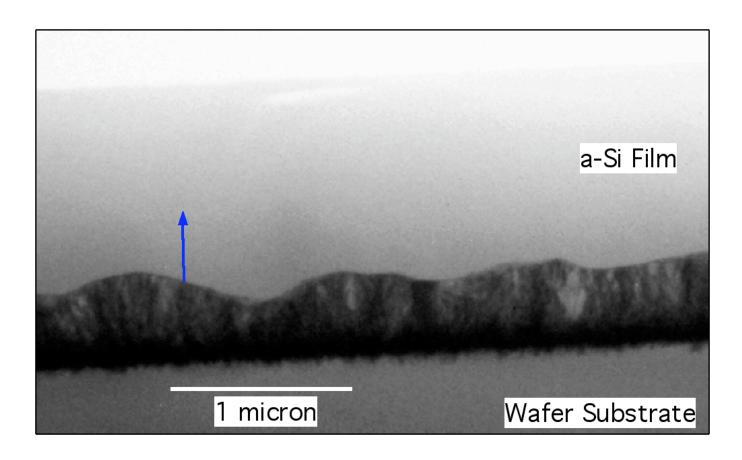


Initial experiments: Start with CeO₂ grown on single crystal YSZ substrates.

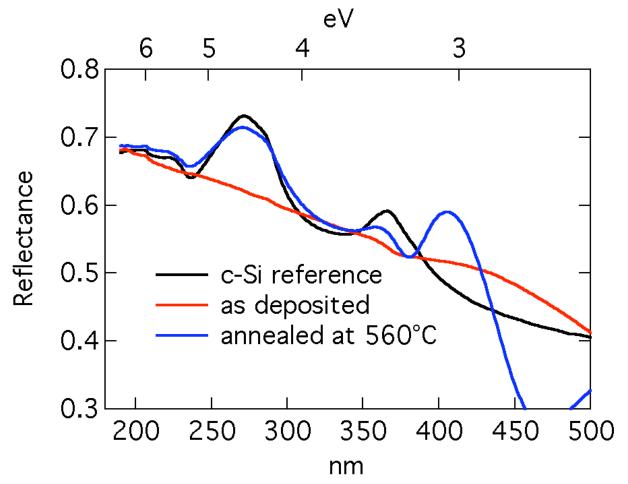
Our goal is to study the CeO₂/Si interface

Solid phase epitaxy demonstrated on wafers

- Direct epitaxial growth
- Solid phase epitaxy: annealing an amorphous film

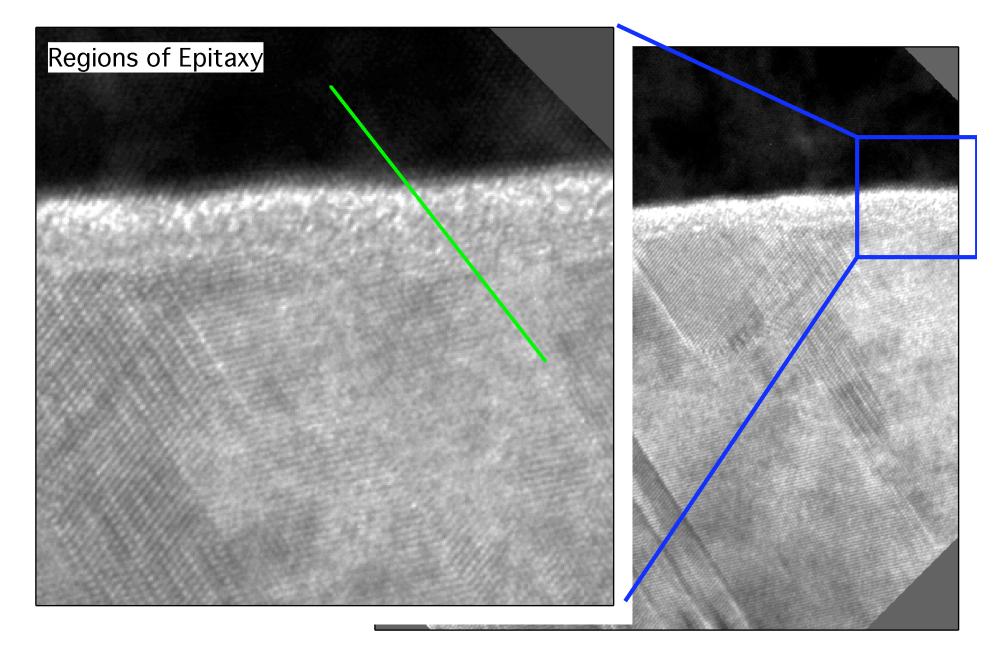


As-deposited, the bulk of silicon films deposited on YSZ/CeO₂ are a-Si:H



After annealing, the film is crystalline ...

TEM very encouraging



Template approach to c-Si on glass A work in progress

Next Steps

- 1. How much epitaxy is possible?
- 2. SiO_x formation
- 3. HWCVD deposition conditions
- 4. Do we need direct growth heteroepitaxy?
- 5. Grow CeO₂ on glass

